



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: John T. Moore et al. § Group Art Unit: 2811
Serial No.: 09/496,794 §
Filed: February 2, 2000 §
For: Trench Isolation for §
Semiconductor Devices § Atty. Dkt. No.: MCT.0005D1US
97-0608

2811
#19/E
Amend to
y Robinson
6/3/03

Mail Stop Non-Fee Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

REPLY TO PAPER NO. 18

Sir:

In response to the office action mailed April 9, 2003, please amend the above-referenced patent application as follows.

IN THE CLAIMS

Please amend claim 26 as follows:

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26 (Twice Amended). A semiconductor structure, comprising:

E1
a support;
a first material deposited on said support, the first material having a first etch rate;
a trench formed through the first material and into the support;
a trench filler material deposited in the trench, the trench filler material having an etch rate that is less than 1.2 times the first etch rate and substantially similar to or less than the first etch rate.

Date of Deposit: May 23, 2003
I hereby certify under 37 CFR 1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated above and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.
Cynthia L. Hayden
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